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N-Channel 70 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (m Ω) Typ.	I _D (A) ^a	Q _g (Typ.)		
70	5.1 at V _{GS} = 10 V	74	57 nC		

Bottom View

DFN5X6

Top View

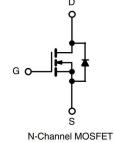
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested



APPLICATIONS

- Primary Side Switching
- Synchronous Rectification
- DC/DC Converters
- **Boost Converters**
- DC/AC Inverters



S	1 •	8] D
S [2	7] D
S	3	6 D
G [4	5] D



ABSOLUTE MAXIMUM RATINGS (7	$\Gamma_A = 25 ^{\circ}\text{C}, unle$	ess otherwise r	noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	70	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	$T_C = 25 ^{\circ}\text{C}$ $T_C = 70 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$	I _D	74 ^a 56 ^a 47 ^{b, c}	_	
Pulsed Drain Current (t = 100 μs)	T _A = 70 °C	I _{DM}	35.5 ^{b, c} 305	A	
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I _S	74 ^a 33.2 ^{b, c}		
Avalanche Current	L = 0.1 mH	I _{AR}	74	7	
Repetitive avalanche energy	L=0.1 IIII	E _{AR}	220	mJ	
Maximum Power Dissipation	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	P _D	59.9 34.6 30.2 ^{b, c} 10.7 ^{b, c}	w	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	
Soldering Recommendations (Peak Temperature)			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^b	t ≤ 10 s	R_{thJA}	30	43	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.5	2.5	C/ W	

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s.



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	70			V		
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		41		mV/°C		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	ι _D = 230 μΑ		- 5.5				
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
	2	$V_{DS} = 70 \text{ V}, V_{GS} = 0 \text{ V}$			1	μА		
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 70 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		5.1	6.2	mΩ		
		$V_{GS} = 7.5 \text{ V}, I_D = 10 \text{ A}$		6	7			
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		87		S		
Dynamic ^b								
Input Capacitance	C _{iss}			3150		pF		
Output Capacitance	C _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		830				
Reverse Transfer Capacitance	C _{rss}			29				
Total Gate Charge		$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		57				
Total Gate Charge	Q _g			53]		
Gate-Source Charge	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 7.5 \text{ V}, I_{D} = 10 \text{ A}$		21		nC		
Gate-Drain Charge	Q_{gd}			16				
Gate Resistance	R_g	f = 1 MHz		4		Ω		
Turn-On Delay Time	t _{d(on)}			18				
Rise Time	t _r	V_{DD} = 30 V, R_L = 3 Ω		85		ns		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 40 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		46				
Fall Time	t _f			77				
Drain-Source Body Diode Characteristic	s							
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			74	Α		
Pulse Diode Forward Current ($t_p = 100 \mu s$)	I _{SM}				305			
Body Diode Voltage	V _{SD}	I _S = 5 A		0.7	1.2	V		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 40 A, dl/dt = 100 A/μs, T _J = 25 °C		36		ns		
Body Diode Reverse Recovery Charge	Q _{rr}	1 το Λ, αι/αι - 100 Λ/μο, 1 _J - 20 °C		42		nC		

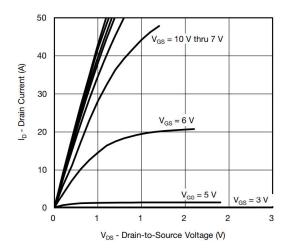
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

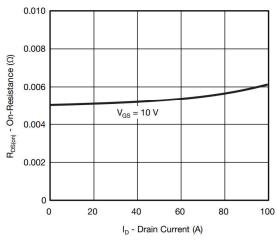
a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.



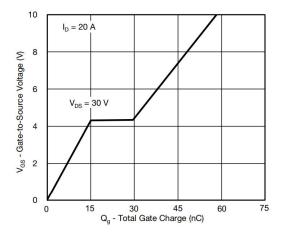
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



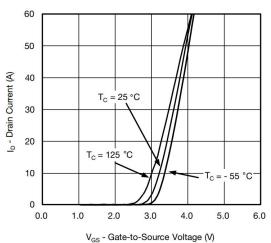
Output Characteristics



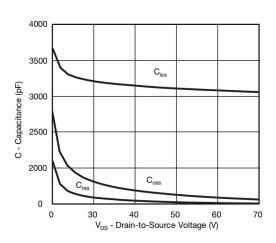
On-Resistance vs. Drain Current



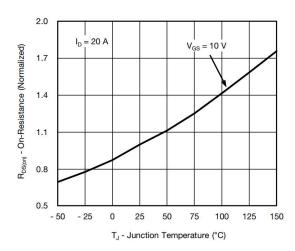
Gate Charge



Transfer Characteristics



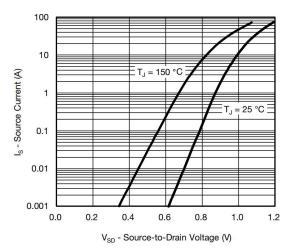
Capacitance



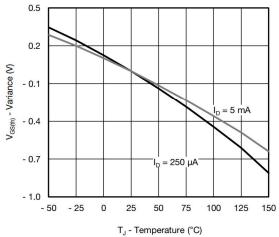
On-Resistance vs. Junction Temperature



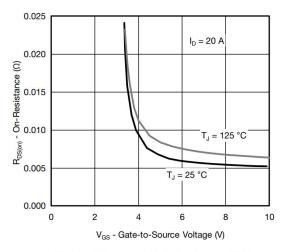
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



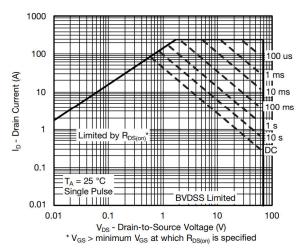
Source-Drain Diode Forward Voltage



Threshold Voltage



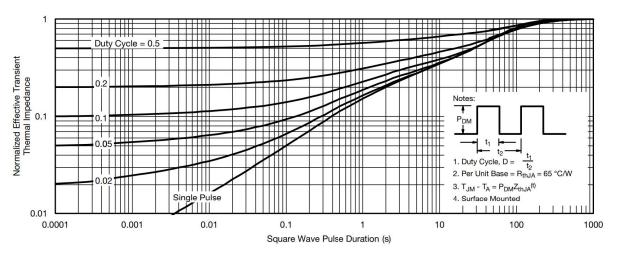
On-Resistance vs. Gate-to-Source Voltage



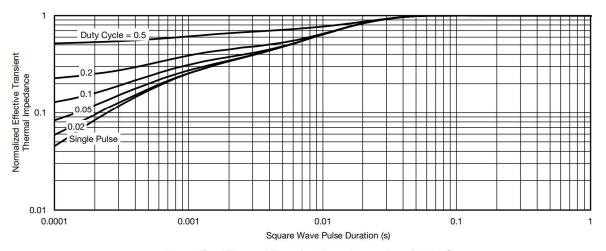
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

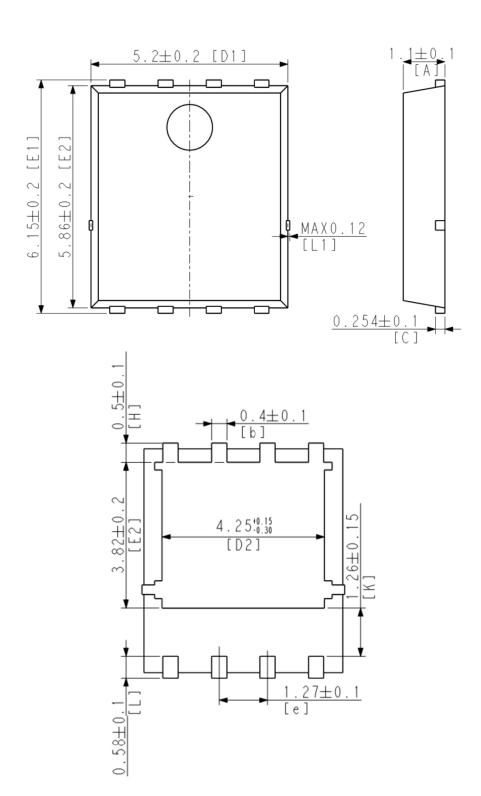


Normalized Thermal Transient Impedance, Junction-to-Case



DFN5X6_8L PACKAGE OUTLINE

Unit:mm







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